

(19)



JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: **61032535 A**

(43) Date of publication of application: **15.02.86**

(51) Int. Cl. **H01L 21/60**
H01L 23/28
H01L 31/02

(21) Application number: **59154956**

(22) Date of filing: **25.07.84**

(71) Applicant: **SANYO ELECTRIC CO**
LTDTOKYO SANYO ELECTRIC CO
LTD

(72) Inventor: **TANAKA TADAHICO**

(54) **MANUFACTURE OF SENSOR**

COPYRIGHT: (C)1986, JPO&Japio

(57) Abstract:

PURPOSE: To eliminate any dispersion in outer shape by utilizing a transfer mold while exposing a sensor layer more precisely by a method wherein an insulating layer is formed by means of photoetching process.

CONSTITUTION: The surface of a sensor layer 2 to be exposed formed on an insulating substrate 1 comprising a thermooxide film of a silicon single crystal substrate is coated with an insulating layer 3. The insulating layer 3 is precisely formed by means of photoetching process after the overall surface thereof is coated with applicable polyimide resin or rubber base resin. Firstly the silicon substrate is bonded on a header 4 to connect a sensor electrode terminal to an outer lead 5 with a bonding wire 6. Secondly the substrate is placed in a specific metal mold to be transfer-molded. At this time, a part of the metal mold abuts against the insulating layer 3 to put the bonding wire 6 in a cavity. Thirdly the cavity is implanted with mold resin to bury the bonding wire 6 completely in a resin layer 7. Finally the insulating layer 3 may be removed by means of plasma etching process to expose the sensor layer 2 only.

